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FS4884  
40V/10A Dual N-Channel MOSFET

## Features

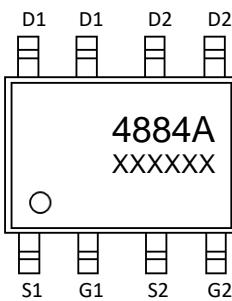
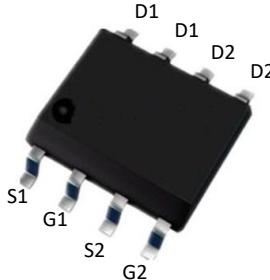
- Trench Power LV MOSFET technology
- High Density Cell Design for Low  $R_{DS(ON)}$
- High Speed switching

## Product Summary

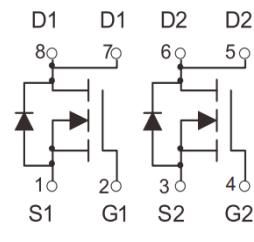
$V_{DS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40V	17mΩ@10V	10A
	25mΩ@4.5V	

## Application

- Battery protection
- Load switch
- Power management

4884A: Device code  
XXXXXX: Code

SOP-8 top view



Schematic diagram



Pb-Free



RoHS



Halogen-Free

Marking and pin assignment

## Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
<b>Common Ratings (TC=25°C Unless Otherwise Noted)</b>			
$V_{DS}$	Drain-Source Breakdown Voltage	40	V
$V_{GS}$	Gate-Source Voltage	±20	V
$T_J$	Maximum Junction Temperature	150	°C
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$I_S$	Diode Continuous Forward Current	10	A
<b>Mounted on Large Heat Sink</b>			
$I_{DM}$	Pulse Drain Current Tested	50	A
$I_D$	Continuous Drain Current@GS=10V	10	A
$P_D$	Maximum Power Dissipation	2	W
$R_{θJA}$	Thermal Resistance Junction-Ambient(*1 in2 Pad of 2-oz Copper), Max.)	60	°C/W

## Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
FS4884	SOP-8	4884A	3,000	6,000	42,000	13" reel



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FS4884  
40V/10A Dual N-Channel MOSFET**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>Static Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)</b>						
BV <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, ID=250μA	40	--	--	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	--	--	1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	--	--	±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , ID=250μA	1	1.5	2.5	V
R <sub>DS(on)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =10V, ID=10A	--	13	17	mΩ
		V <sub>GS</sub> =4.5V, ID=10A	--	19	25	

**Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)**

C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, f=1MHz	--	965	--	pF
C <sub>OSS</sub>	Output Capacitance		--	110	--	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance		--	95	--	pF

**Switching Characteristics**

Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =20V, ID=8A, V <sub>GS</sub> =10V	--	23	--	nC
Q <sub>gs</sub>	Gate Source Charge		--	3.5	--	nC
Q <sub>gd</sub>	Gate Drain Charge		--	5.5	--	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =20V, RL=2.5Ω, V <sub>GS</sub> =10V, RG=3Ω	--	5.5	--	nS
t <sub>r</sub>	Turn-on Rise Time		--	15	--	nS
t <sub>d(off)</sub>	Turn-Off Delay Time		--	25	--	nS
t <sub>f</sub>	Turn-Off Fall Time		--	12	--	nS

**Source-Drain Diode Characteristics**

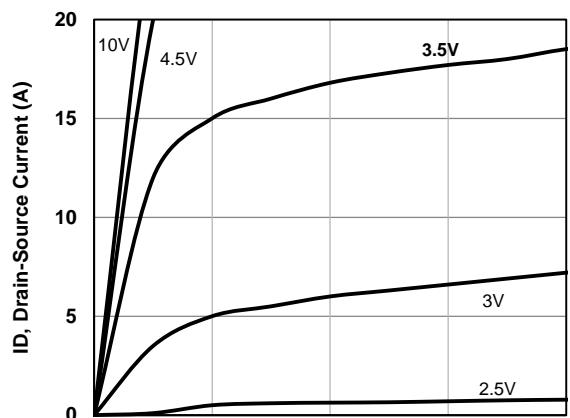
V <sub>SD</sub>	Forward on voltage	T <sub>J</sub> =25°C, I <sub>S</sub> =10A,	--	--	1.2	V
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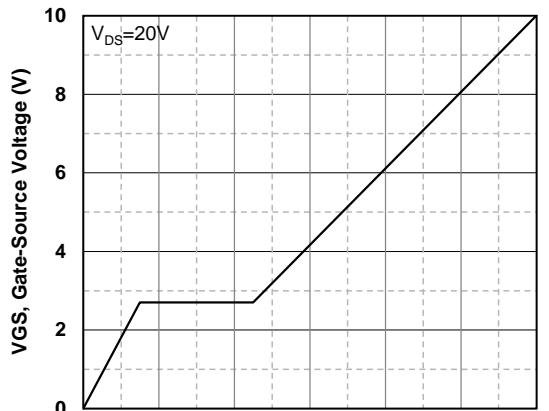
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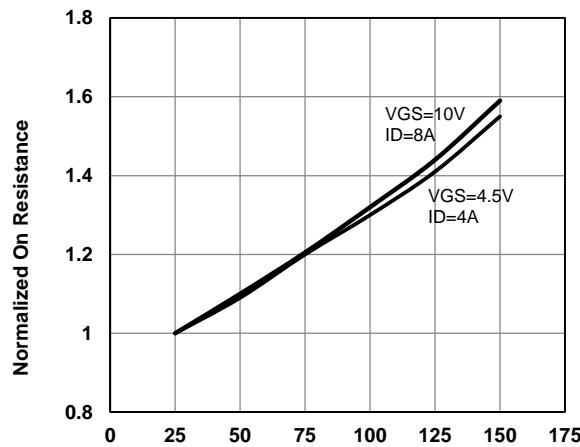
## Typical Operating Characteristics



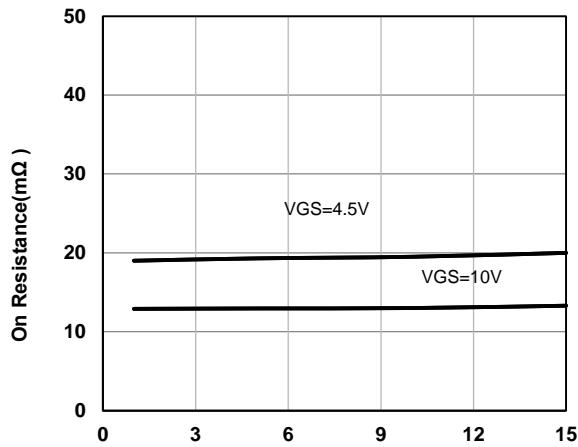
V<sub>DS</sub>, Drain -Source Voltage (V)  
Fig1. Typical Output Characteristics



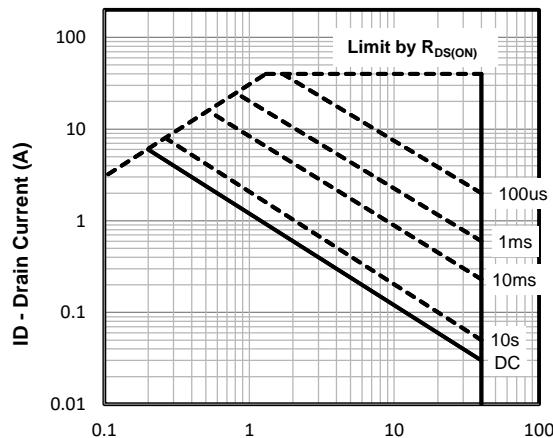
Q<sub>g</sub> -Total Gate Charge (nC)  
Fig2. Typical Gate Charge Vs.Gate-Source Voltage



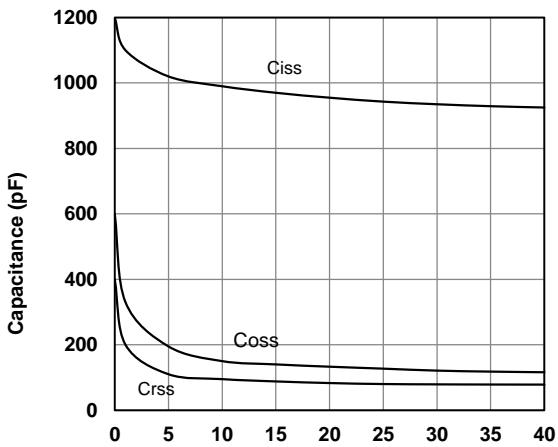
T<sub>j</sub> - Junction Temperature (°C)  
Fig3. Normalized On-Resistance Vs. Temperature



ID, Drain-Source Current (A)  
Fig4. On-Resistance Vs. Drain-Source Current



V<sub>DS</sub>, Drain -Source Voltage (V)  
Fig5. Maximum Safe Operating Area



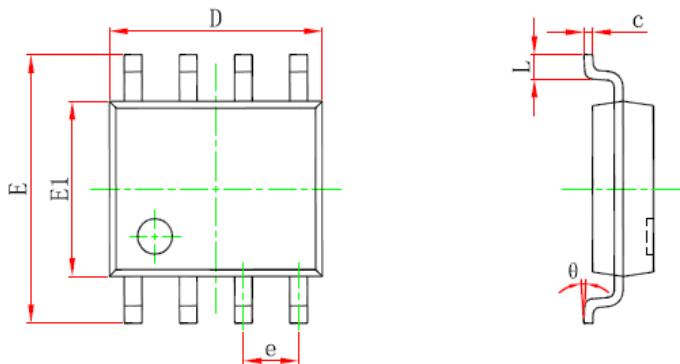
V<sub>D</sub> , Drain-Source Voltage (V)  
Fig6 Typical Capacitance Vs.Drain-Source Voltage



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## SOP-8 Package information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.450	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.700	5.100	0.185	0.201
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°